



DMN5/L06VK/L06VAK/010VAK

DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Dual N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage, 1.0V Max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- . ESD Protected up to 2kV
- Qualified to AEC-Q101 Standards for High Reliability

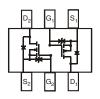


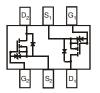


SOT563 Top View

Mechanical Data

- Case: SOT563
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.006 grams (Approximate)





DMN5L06VK

DMN5L06VAK DMN5010VAK

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN5L06VK-7	SOT563	3,000/Tape & Reel
DMN5L06VK-7A	SOT563	3,000/Tape & Reel
DMN5L06VK-13	SOT563	10,000/Tape & Reel
DMN5L06VK-13A	SOT563	10,000/Tape & Reel
DMN5L06VAK-7	SOT563	3,000/Tape & Reel
DMN5L06VAK-7A	SOT563	3,000/Tape & Reel
DMN5L06VAK-13	SOT563	10,000/Tape & Reel
DMN5L06VAK-13A	SOT563	10,000/Tape & Reel
DMN5010VAK-7	SOT563	3,000/Tape & Reel
DMN5010VAK-7A	SOT563	3,000/Tape & Reel
DMN5010VAK-13	SOT563	10,000/Tape & Reel
DMN5010VAK-13A	SOT563	10,000/Tape & Reel

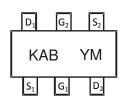
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

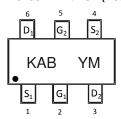


Marking Information (Note 5 & 6)

DMN5L06VK-7/-13 (Note 5)



DMN5L06VK-7A/-13A (Note 6)



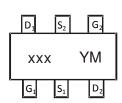
KAB= DMN5L06VK Product Type

Marking Code

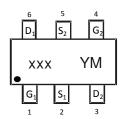
YM = Date Code Marking

Y = Year (ex: E = 2017) M = Month (ex: 9 = September)

DMN5L06VAK-7/-13 (Note 5) DMN5010VAK-7/-13 (Note 5)



DMN5L06VAK-7A/-13A (Note 6) DMN5010VAK-7A/-13A (Note 6)



xxx =Product Type Marking Code: KAE or KAC

YM = Date Code Marking Y = Year (ex: E = 2017)

M = Month (ex: 9 = September)

Date Code Key

Year	2006	~	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025
Code	Т	~	D	Е	F	G	Н	ı	J	K	L	М
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec

5. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).

^{6.} Part number with suffix 7A and 13A designates devices marked with a Pin 1 indicator. There is no other difference between both devices.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain Source Voltage		V_{DSS}	50	V
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$		V_{DGR}	50	V
Gate-Source Voltage	Continuous Pulsed	V _{GSS}	±20 ±40	V
Drain Current (Note 7)	Continuous Pulsed	I _D I _{DM}	280 1.5	mA A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 7)	P_{D}	250	mW
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	500	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

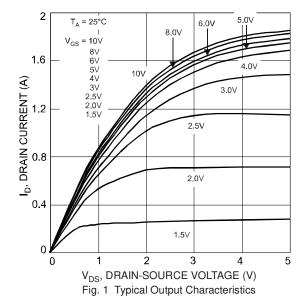
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

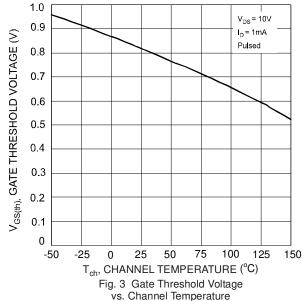
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage	BV _{DSS}	50	_	_	V	$V_{GS} = 0V$, $I_D = 10\mu A$		
Zero Gate Voltage Drain Current @ $T_C = +25$ °C	I _{DSS}		_	60	nA	$V_{DS} = 50V$, $V_{GS} = 0V$		
Gate-Body Leakage	I _{GSS}	l	_	1 500 50	μA nA nA	$V_{GS} = \pm 12V, V_{DS} = 0V$ $V_{GS} = \pm 10V, V_{DS} = 0V$ $V_{GS} = \pm 5V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 8)	ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage $@T_J = +25^{\circ}C$ $@T_J = +0^{\circ}C \text{ to } +85^{\circ}C \text{ (Note 9)}$	V _{GS(TH)}	0.49 0.30	_	1.0 1.2	V	$V_{DS} = V_{GS}, I_D = 250\mu A$		
Static Drain-Source On-Resistance	R _{DS(ON)}		_ _ _	3.0 2.5 2.0	Ω	$V_{GS} = 1.8V, I_D = 50mA$ $V_{GS} = 2.5V, I_D = 50mA$ $V_{GS} = 5.0V, I_D = 50mA$		
On-State Drain Current	I _{D(ON)}	0.5	1.4	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$		
Forward Transconductance	Y _{fs}	200	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$		
Source-Drain Diode Forward Voltage	V _{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_S = 115mA$		
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance	C _{iss}		_	50	pF			
Output Capacitance	Coss	_	_	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz		
Reverse Transfer Capacitance	C _{rss}		_	5.0	pF	7 - 1.0WH12		

7. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.8. Short duration pulse test used to minimize self-heating effect.9. Guaranteed by design. Not subject to product testing. Notes:



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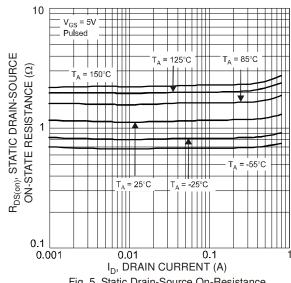
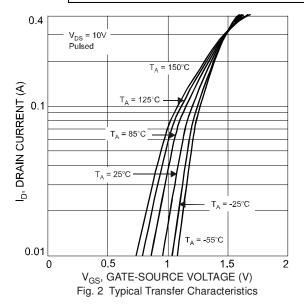


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current



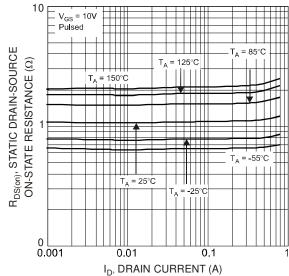


Fig. 4 Static Drain-Source On-Resistance

vs. Drain Current

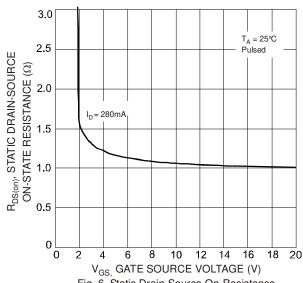


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage





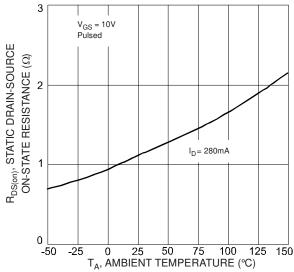
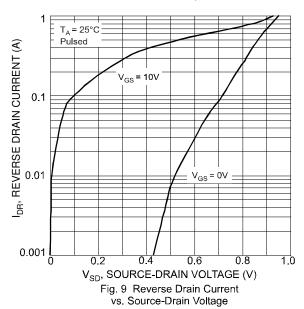
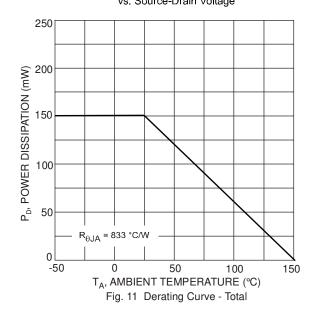


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature





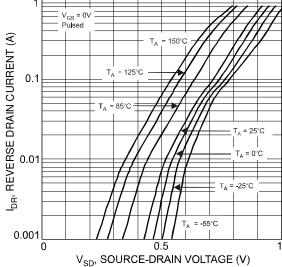


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

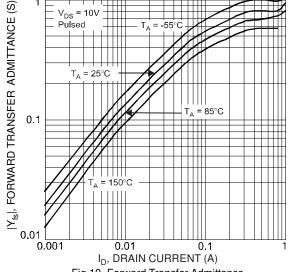
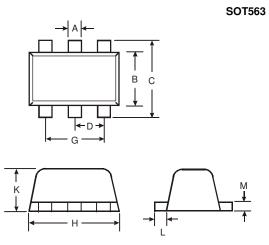


Fig.10 Forward Transfer Admittance vs. Drain Current



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

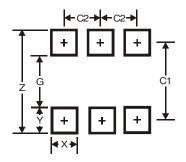


SOT563						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.20			
В	1.10	1.25	1.20			
С	1.55	1.70	1.60			
D	-	-	0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
K	0.55	0.60	0.60			
L	0.10	0.30	0.20			
M	0.10	0.18	0.11			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT563



Dimensions	Value (in mm)		
Z	2.2		
G	1.2		
Х	0.375		
Υ	0.5		
C1	1.7		
C2	0.5		

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